

40V LOW $V_{CE(SAT)}$ NPN SURFACE MOUNT TRANSISTOR
Features

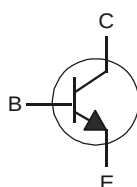
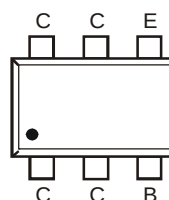
- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- Complementary PNP Type Available (DSS5240Y)
- Ultra Small Surface Mount Package
- **"Lead Free", RoHS Compliant (Note 1)**
- **Halogen and Antimony Free "Green" Device (Note 2)**
- **ESD rating: 400V-MM, 8KV-HBM**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin annealed over Copper Plated Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (approximate)



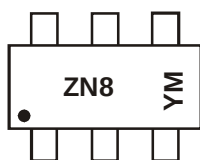
Top View


 Top View
 Device Schematic

 Top View
 Pin Out Configuration

Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DSS4240Y-7	ZN8	7	8mm	3,000

- Notes:
1. No purposefully added lead.
 2. Diode's Inc.'s "Green" policy can be found on our website at <http://www.diodes.com>.
 3. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information


ZN8 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: V = 2008)
 M = Month (ex: 9 = September)

Date Code Key

Year	2010	2011	2012	2013	2014	2015
Code	X	Y	Z	A	B	C

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current - Continuous	I_C	2	A
Peak Pulse Collector Current	I_{CM}	3	A
Peak Base Current	I_{BM}	0.3	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4) @ $T_A = 25^\circ\text{C}$	P_D	625	mW
Thermal Resistance, Junction to Ambient (Note 4) @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Notes: 4. Device mounted on FR-4 PCB, with minimum recommended pad layout.

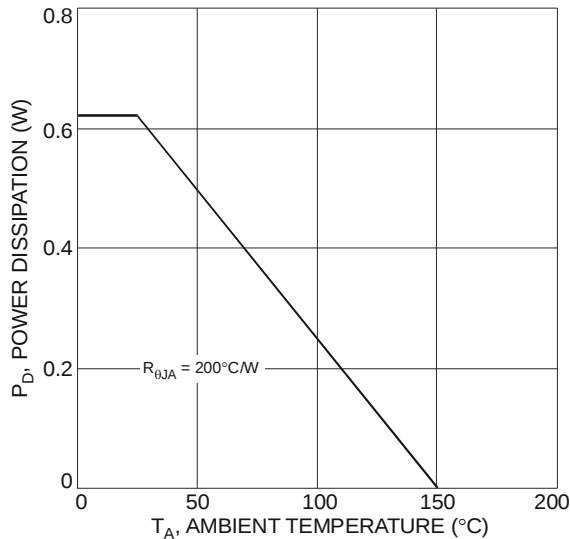


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

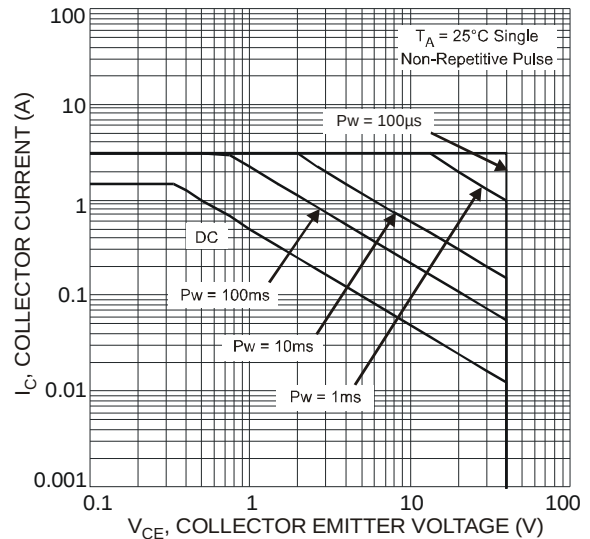


Fig. 2 Safe Operating Area

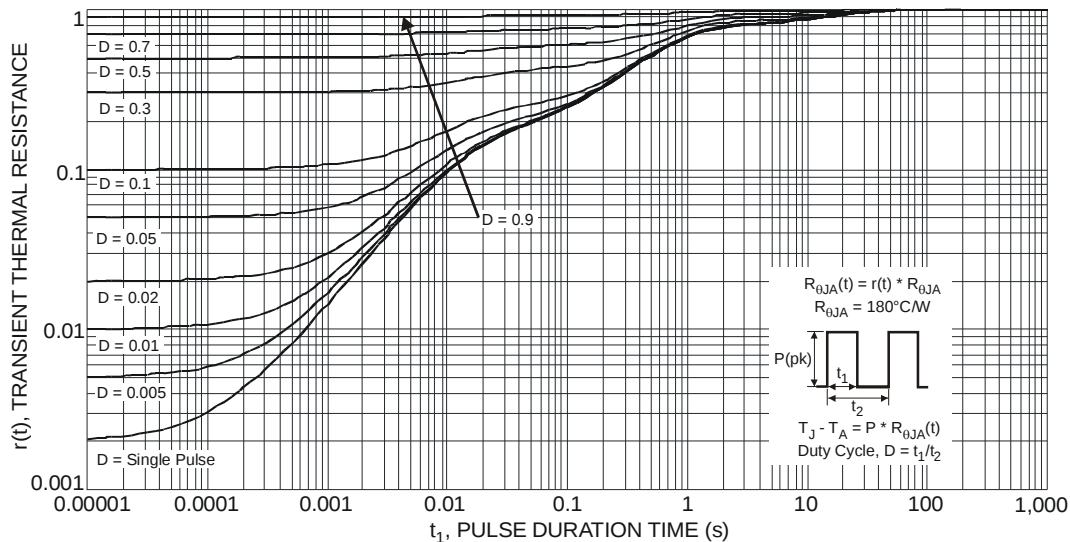


Fig. 3 Transient Thermal Response

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	40	150	—	V	I _C = 100μA, I _E = 0
Collector-Emitter Breakdown Voltage (Note 5)	BV _{CEO}	40	55	—	V	I _C = 10mA, I _B = 0
Emitter-Base Breakdown Voltage	BV _{EBO}	5	8.5	—	V	I _E = 100μA, I _C = 0
Collector Cutoff Current	I _{CBO}	—	—	100 50	nA μA	V _{CB} = 30V, I _E = 0 V _{CB} = 30V, I _E = 0, T _A = 150°C
Emitter Cutoff Current	I _{EBO}	—	—	100	nA	V _{EB} = 4V, I _C = 0
DC Current Gain (Note 5)	h _{FE}	350 300 300 150	— — — —	— — — —	—	V _{CE} = 2V, I _C = 100mA V _{CE} = 2V, I _C = 500mA V _{CE} = 2V, I _C = 1A V _{CE} = 2V, I _C = 2A
Collector-Emitter Saturation Voltage (Note 5)	V _{CE(sat)}	— — — — —	45 52 100 105 190	70 100 180 180 320	mV	I _C = 100mA, I _B = 1mA I _C = 500mA, I _B = 50mA I _C = 750mA, I _B = 15mA I _C = 1A, I _B = 50mA I _C = 2A, I _B = 200mA
Collector-Emitter Saturation Resistance	R _{CE(sat)}	—	105	200	mΩ	I _C = 500mA, I _B = 50mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	—	—	1.1	V	I _C = 2A, I _B = 200mA
Base-Emitter Turn On Voltage	V _{BE(on)}	—	—	0.75	V	V _{CE} = 2V, I _C = 100mA
Output Capacitance	C _{obo}	—	—	20	pF	V _{CB} = 10V, f = 1.0MHz
Current Gain-Bandwidth Product	f _T	100	250	—	MHz	V _{CE} = 10V, I _C = 50mA, f = 100MHz
Turn-On Time	t _{on}	—	64	—	ns	V _{CC} = 10V I _C = 1A, I _{B1} = -I _{B2} = 50mA
Delay Time	t _d	—	20	—	ns	
Rise Time	t _r	—	44	—	ns	
Turn-Off Time	t _{off}	—	315	—	ns	
Storage Time	t _s	—	275	—	ns	
Fall Time	t _f	—	40	—	ns	

Notes: 5. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.

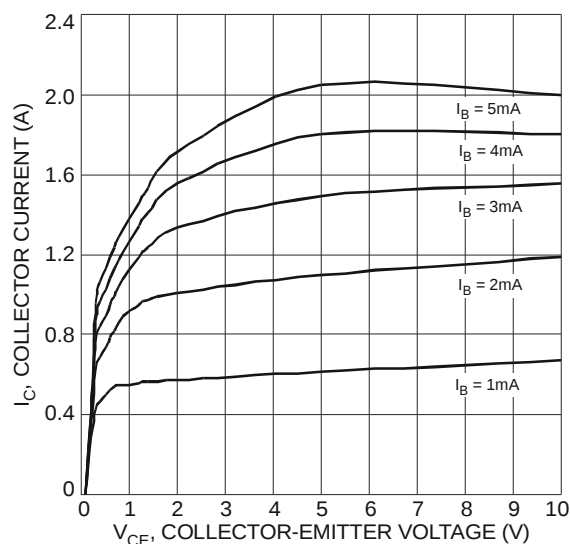


Fig. 4 Typical Collector Current vs. Collector-Emitter Voltage

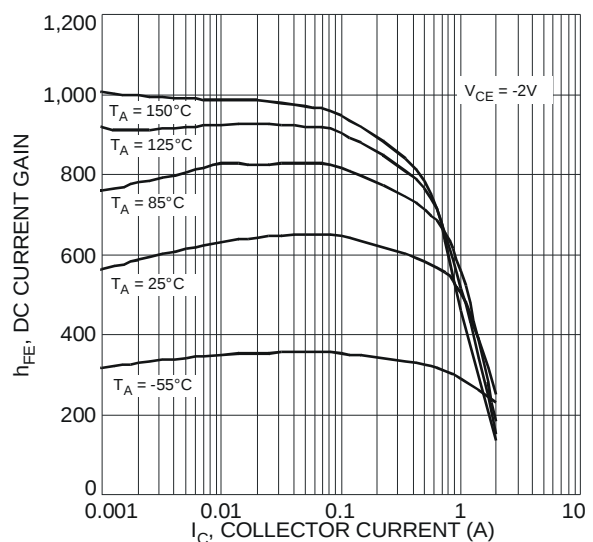


Fig. 5 Typical DC Current Gain vs. Collector Current

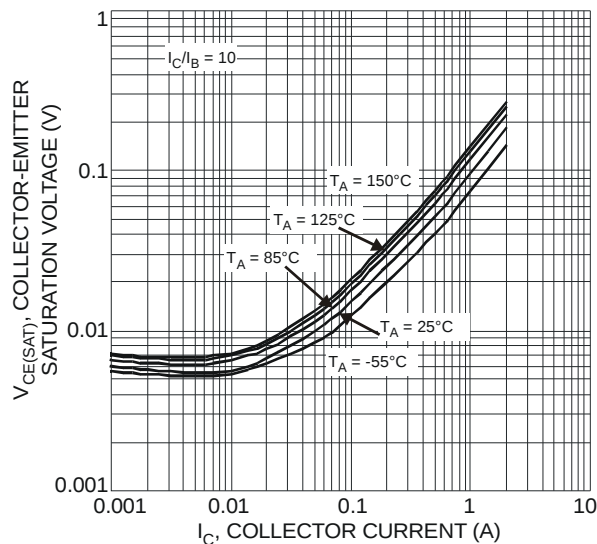


Fig. 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current

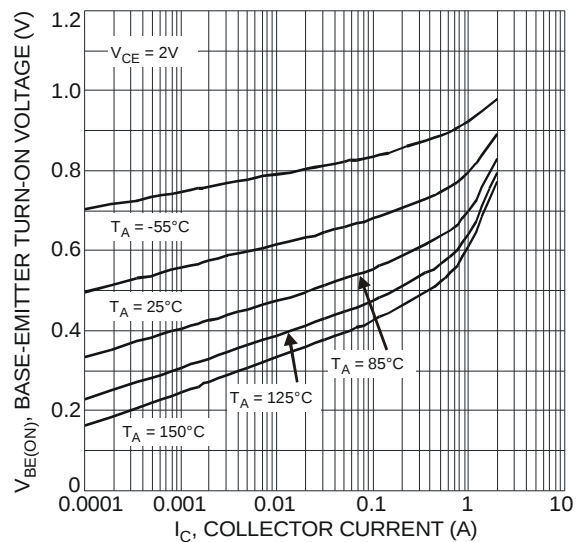


Fig. 7 Typical Base-Emitter Turn-On Voltage vs. Collector Current

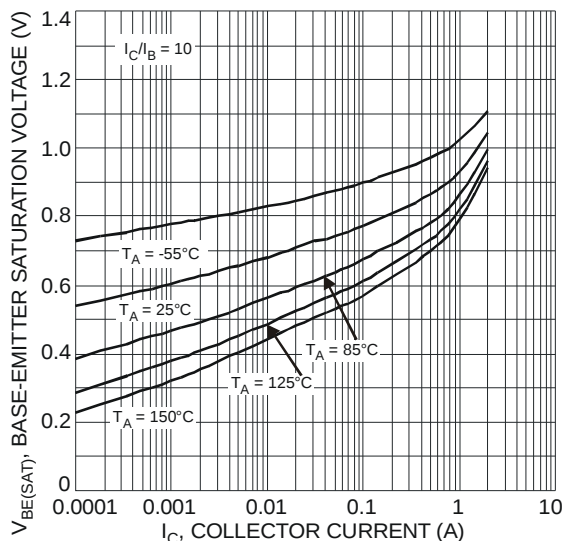


Fig. 8 Typical Base-Emitter Saturation Voltage vs. Collector Current

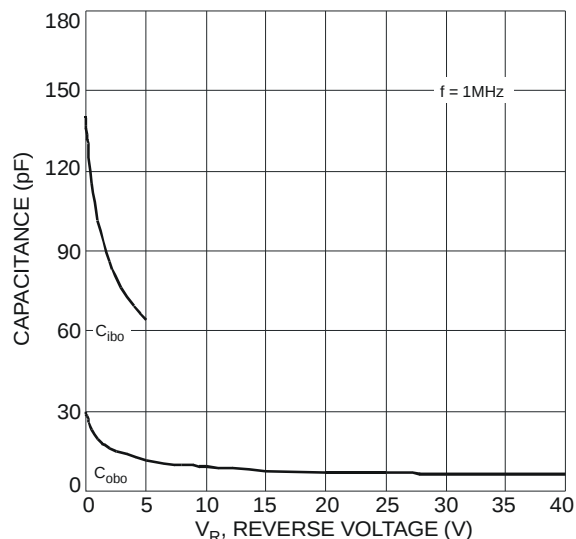
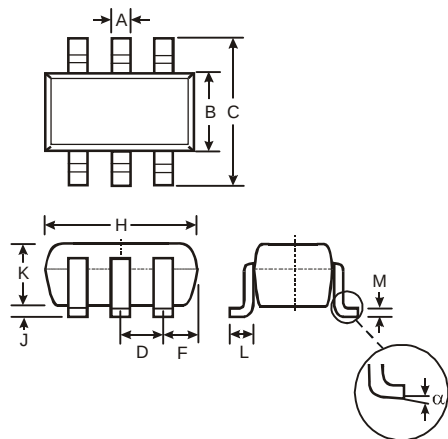


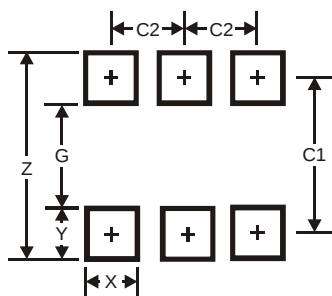
Fig. 9 Typical Capacitance Characteristics

Package Outline Dimensions



SOT363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Typ	
F	0.40	0.45
H	1.80	2.20
J	0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.22
α	0°	8°
All Dimensions in mm		

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C1	1.9
C2	0.65

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9